



BYW29G-200

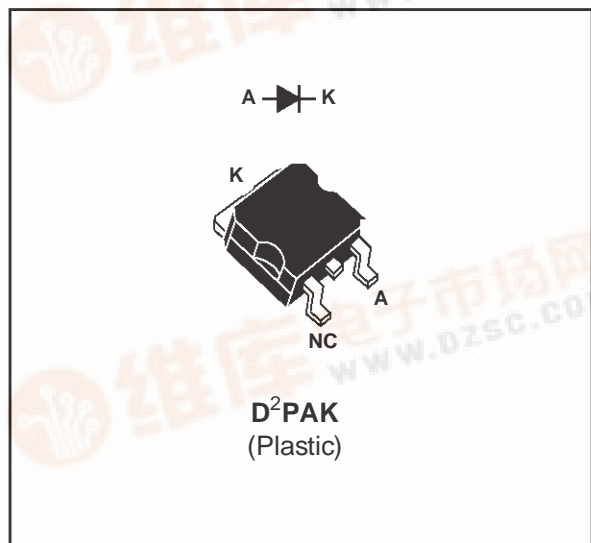
HIGH EFFICIENCY FAST RECOVERY DIODES

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	8 A
V_{RRM}	200 V
t_{rr}	35 ns
V_F	0.85 V

FEATURES AND BENEFITS

- VERY SMALL CONDUCTION LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD AND REVERSE RECOVERY TIMES
- HIGH SURGE CURRENT
- SMD



DESCRIPTION

Single rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in a surface mount package D²PAK, this device is intended for use in high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		200	V
$I_{F(RMS)}$	RMS forward current		16	A
$I_{F(AV)}$	Average forward current	$T_c=120^{\circ}C$ $\delta = 0.5$	8	A
I_{FSM}	Surge non repetitive forward current (All pins connected)	$t_p=10ms$ sinusoidal	80	A
I_{FRM}	Repetitive peak forward current	$t_p = 5 \mu s$ $f = 5 kHz$	75	A
T_{stg} T_j	Storage and junction temperature range		- 40 to + 150	$^{\circ}C$



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THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-c)	Junction to case thermal resistance	2.8	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = V _{RRM}	T _j = 25°C		10	μA
			T _j = 100°C		0.6	mA
V _F **	Forward voltage drop	I _F = 5 A	T _j = 125°C		0.85	V
		I _F = 10 A	T _j = 125°C		1.05	
		I _F = 10 A	T _j = 25°C		1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %
 ** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :
 $P = 0.65 \times I_{F(AV)} + 0.040 I_{F(RMS)}^2$

RECOVERY CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{rr}	Reverse recovery time	T _j = 25°C I _F = 0.5A I _{rr} = 0.25 A I _R = 1A			25	ns
		T _j = 25°C I _F = 1A dI _F /dt = -50A/μs V _R = 30V			35	
t _{fr}	Forward recovery time	T _j = 25°C I _F = 1A dI _F /dt = 100A/μs V _{FR} = 1.1 x V _F max		15		ns
V _{FP}	Peak forward voltage	T _j = 25°C I _F = 1A dI _F /dt = 100A/μs		2		V

PIN OUT configuration in D²PAK:



Fig.1 : Average forward power dissipation versus average forward current.

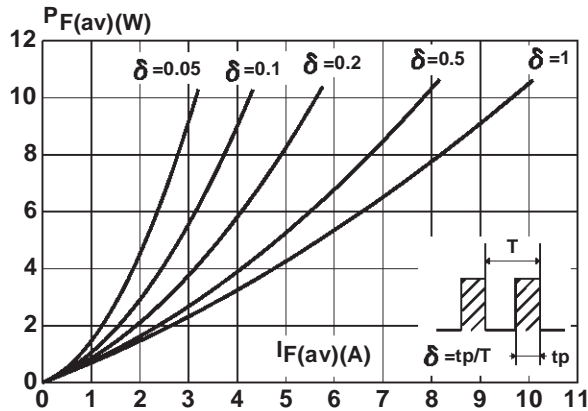


Fig.2 : Peak current versus form factor.

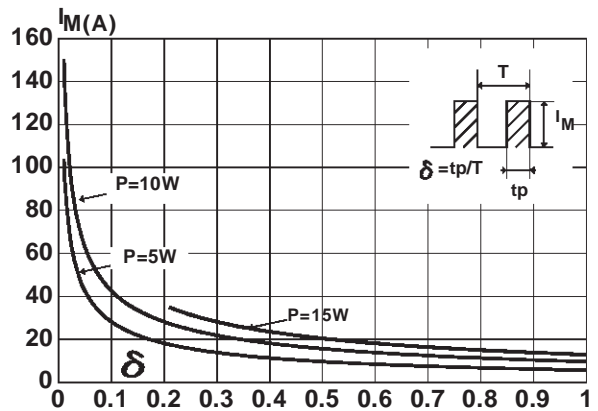


Fig.3 : Forward voltage drop versus forward current (maximum values).

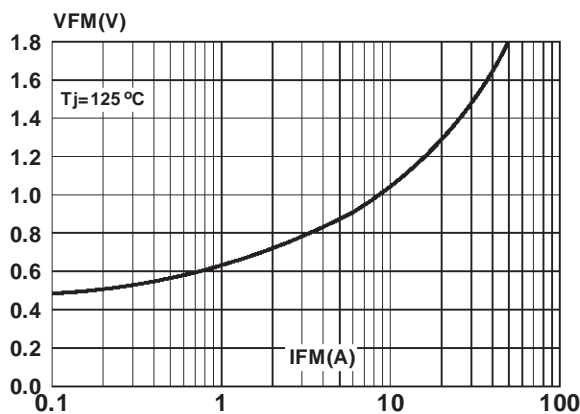


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

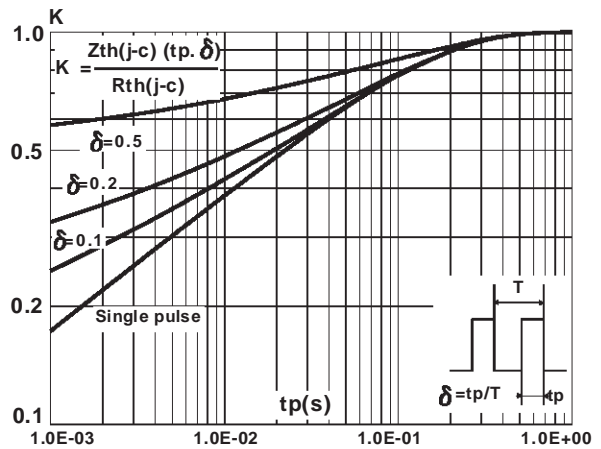


Fig.5 : Non repetitive surge peak forward current versus overload duration.

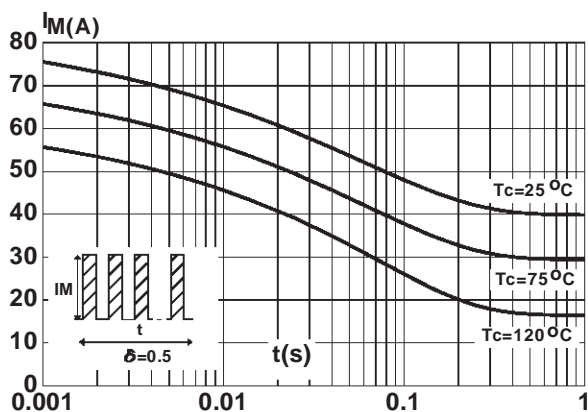


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)

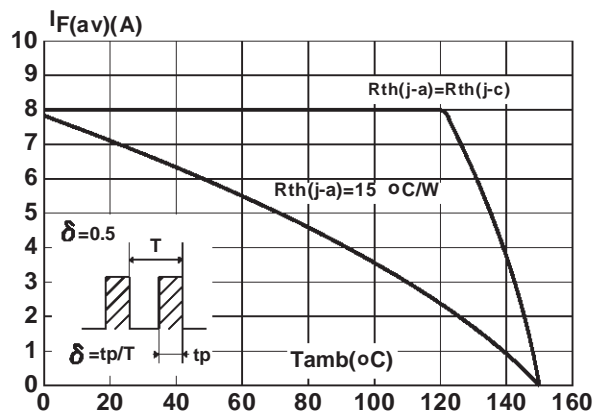


Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

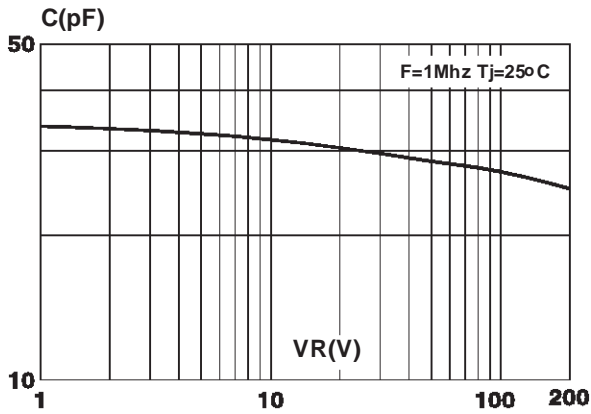


Fig.8 : Recovery charges versus dI_F/dt .

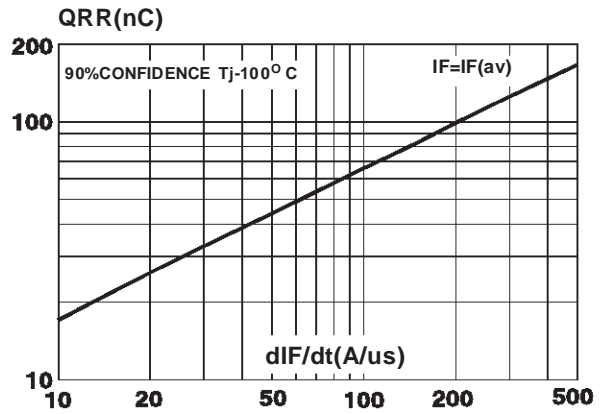


Fig.9 : Peak reverse current versus dI_F/dt .

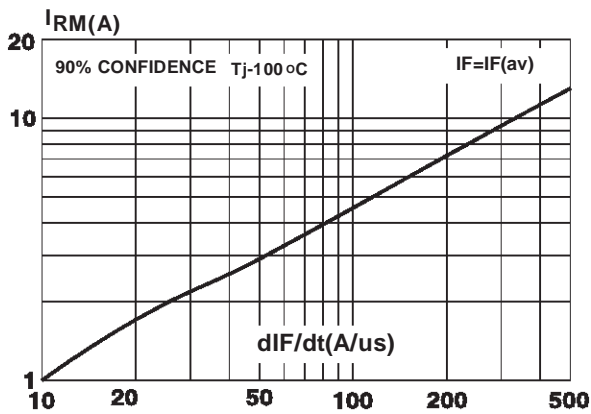
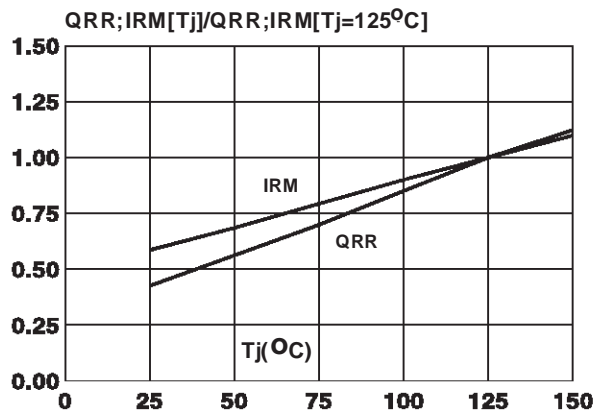
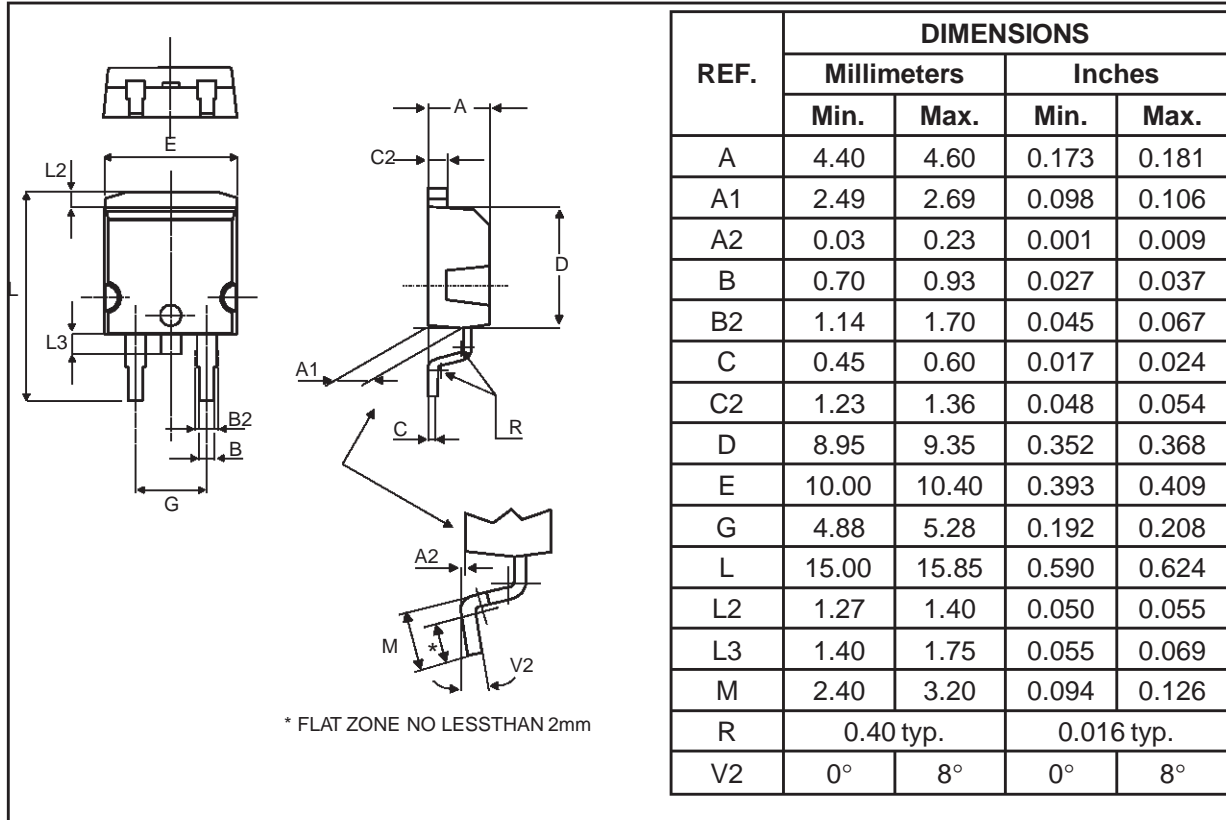


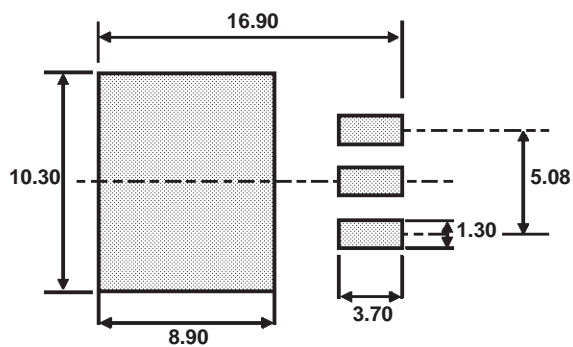
Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
D²PAK (Plastic)



FOOT PRINT (in millimeters)



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